

Supporting information

A Novel Defect-Selective Etching Method for β -Ga₂O₃ Single Crystals Based on Hydrofluoric Acid

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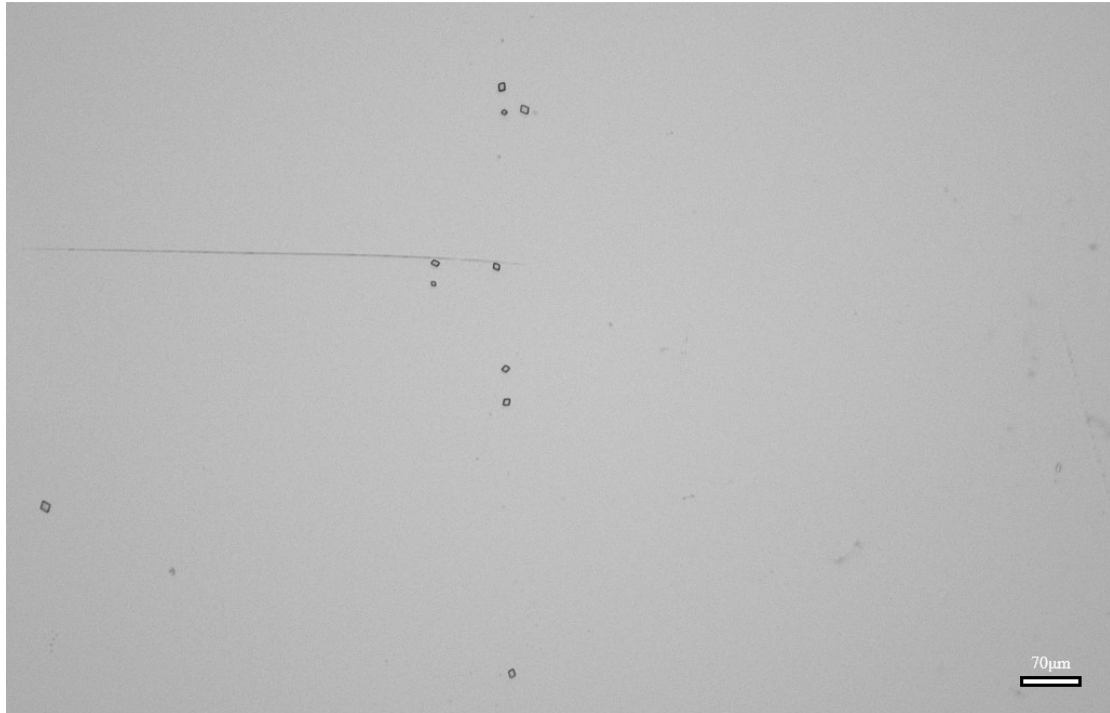


Fig. S1 Optical microscope image of the (001)-oriented surface etched in mixed solution of HF and HNO₃ at 60 °C for 4h

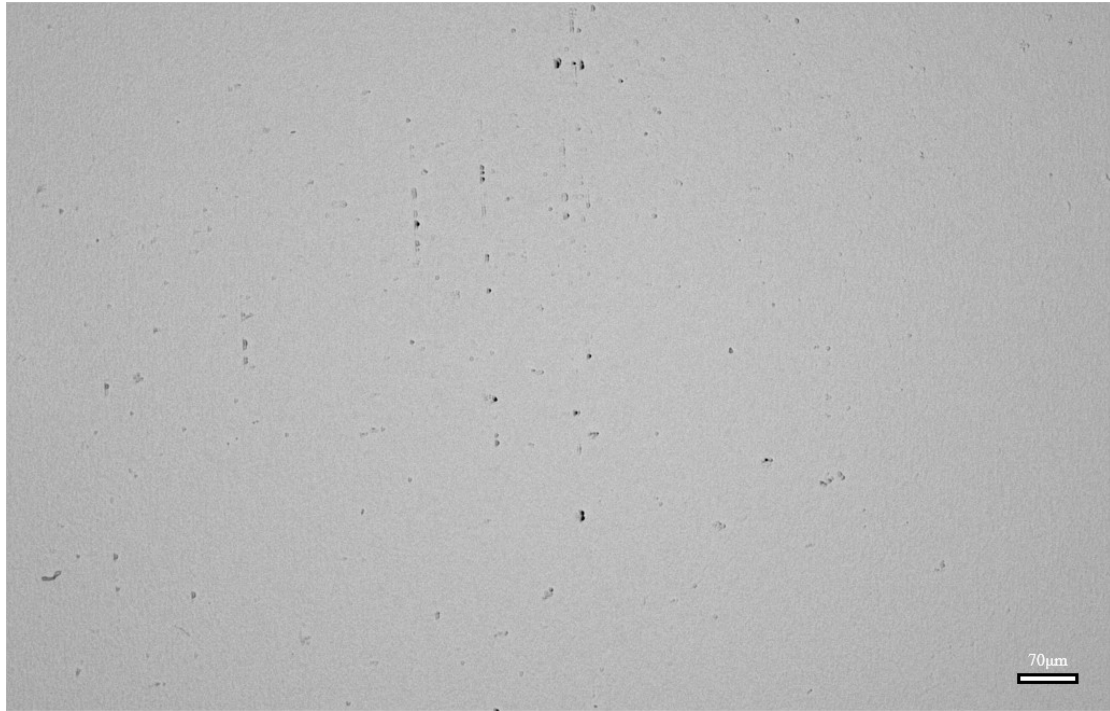


Fig. S2 Optical microscope image of the $(\bar{2}01)$ -oriented surface etched in mixed solution of HF and HNO_3 at 60 °C for 4h



Fig. S3 Optical microscope image of the (010)-oriented surface etched in mixed solution of HF and HNO₃ at 60 °C for 4h